Peak gate power	P_{GM}	5	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	0.5	kV

NOTE 1: Operating junction temperature T_j is up to 125 when a resistor ≤1kΩ is connected between Gate and Cathode. Without this resistor, the T_j is up to 110 only.

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
GT					

ORDERING INFORMATION

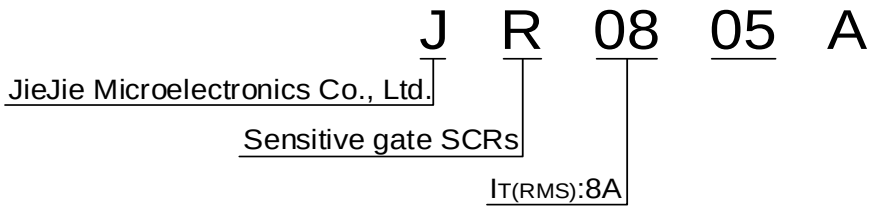


FIG.1: Maximum power dissipation versus RMS on-state current

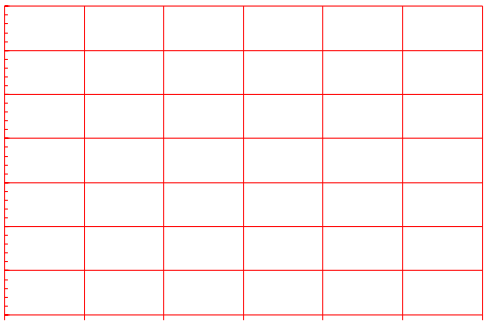
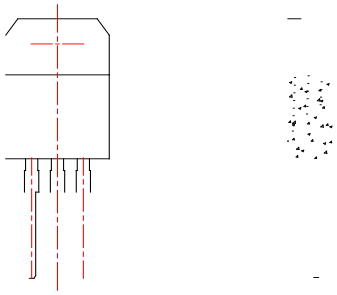


FIG.2: RMS on-state current versus case temperature

PACKAGE MECHANICAL DATA



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